2SC1624

SILICON NPN PLANAR TYPE

9097250 TOSHIBA (DISCRETE/OPTO)

MEDIUM POWER AMPLIFIER APPLICATIONS. DRIVER STAGE AMPLIFIER APPLICATIONS.

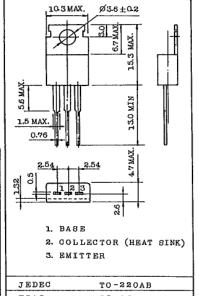
FEATURES:

High Breakdown Voltage: VCEO=120V (2SC1624) Complementary to 2SA814 and 2SA815.

MAXIMUM RATINGS (Ta=25°C)

TOPETHON TOTT THE	(1a-25 C)			
CHARACTE	SYMBOL	RATING	UNIT	
Collector-Base	2SC1624		120	
Voltage	2SC1625	v _{сво}	100	
Collector-	2SC16 24		120	v
Emitter Voltage	2SC16 25	- v _{CEO}	100	\
Emitter-Base Voltage		v_{EBO}	5	v
Collector Current		IC	1	A
Emitter Current		$I_{\rm E}$	-1	A
Collector Power Dissipation (Tc=25°C)		PC	15	W
Junction Temperature		Tj	150	°C
Storage Temperature Range		Tstg	-55∿150	°C

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EIAJ 80-46 TOSHIBA 2-10A1A

Mounting Kit No. AC75

Weight: 1.9g

ELECTRICAL CHARACTERISTICS (Ta=25°C)

ELECTRIC OTTO							
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I _{CBO}	$V_{CB}=50V$, $I_{E}=0$	-	-	1.0	ДĄ
Emitter Cut-off Current		IEBO	VEB=5V, IC=0	-	-	1.0	μA
Collector- Emitter Breakdown Voltage	2SC1624	V _{(BR)CEO}	$I_C=10$ mA, $I_B=0$	120	-	-	v
	2SC1625			100	_	-	
Emitter-Base Breakdown Voltage		V(BR)EBO	I _E =1mA, I _C =0	5	-	_	v
DC Current Gain		hFE(1) (Note)	V _{CE} =5V, I _C =150mA	70	-	240	
		hFE(2)	VCE=5V, IC=500mA	40		-]
Collector-Emitter Saturation Voltage		V _{CE(sat)}	I _C =500mA, I _B =50mA	-	-	0.5	v
Base-Emitter Voltage		VBE	V _{CE} =5V, I _C =500mA	-	-	1.0	V
Transition Frequency f _T		f_{T}	VCE=5V, IC=150mA	10	30	_	MHz
Collector Output Capacitance Cob		Cob	VCB=10V, IE=0, f=1 MHz	-	20		pF

Note: $h_{FE(1)}$ Classification 0: $70\sim140$, Y: $120\sim240$

COLLECTOR-EMITTER VOLTAGE VCE (V)

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